BUJ303CD

NPN power transistor

8 November 2012

Product data sheet

1. Product profile

1.1 General description

High voltage high speed planar passivated NPN power switching transistor in a SOT428 (DPAK) surface mountable plastic package.

1.2 Features and benefits

- Fast switching
- Low thermal resistance
- Surface mountable package
- Tight DC gain spreads
- Very high voltage capability
- · Very low switching and conduction losses

1.3 Applications

- DC-to-DC converters
- High frequency electronic lighting ballasts
- Inverters
- · Motor control systems

1.4 Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-------------------|--------------------------------|---|-----|-----|------|----------|
| I _C | collector current | Fig. 1; Fig. 2; Fig. 4 | - | - | 5 | Α |
| P _{tot} | total power dissipation | T _{mb} ≤ 25 °C; <u>Fig. 3</u> | - | - | 80 | W |
| V _{CESM} | collector-emitter peak voltage | V _{BE} = 0 V | - | - | 1050 | V |
| Static characte | eristics | | | | | <u> </u> |
| h _{FE} | DC current gain | I _C = 10 mA; V _{CE} = 3 V; T _{mb} = 25 °C; Fig. 12 | 28 | 34 | 47 | |
| | | I _C = 250 mA; V _{CE} = 3 V; T _{mb} = 25 °C; Fig. 12 | 35 | 43 | 57 | |
| | | I _C = 800 mA; V _{CE} = 3 V; T _{mb} = 25 °C; Fig. 12 | 31 | 37 | 48 | |





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2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|---------------------------------------|--------------------|----------------|
| 1 | В | base | mb | C |
| 2 | С | collector[1] | | В |
| 3 | Е | emitter | | - 1 |
| mb | С | mounting base; connected to collector | 1 3 DPAK (SOT428) | E sym123 |

[1] it is not possible to make a connection to pin 2 of the SOT428 (DPAK) package.

3. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|-------------|---------|---|---------|
| | Name | Description | Version |
| BUJ303CD | DPAK | plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped) | SOT428 |

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|-------------------|--------------------------------|--|-----|------|------|
| V _{CESM} | collector-emitter peak voltage | V _{BE} = 0 V | - | 1050 | V |
| V _{CEO} | collector-emitter voltage | I _B = 0 A | - | 400 | V |
| I _C | collector current | Fig. 1; Fig. 2; Fig. 4 | - | 5 | Α |
| I _{CM} | peak collector current | | - | 10 | Α |
| I _B | base current | | - | 2 | Α |
| I _{BM} | peak base current | | - | 4 | Α |
| P _{tot} | total power dissipation | T _{mb} ≤ 25 °C; <u>Fig. 3</u> | - | 80 | W |
| T _{stg} | storage temperature | | -65 | 150 | °C |
| Tj | junction temperature | | - | 150 | °C |

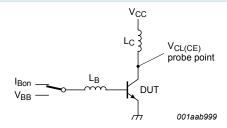


Fig. 1. Test circuit for reverse bias safe operating area

$$\begin{split} V_{\mathit{CL(CE)}} \leq 1000 \; V; V_{\mathit{CC}} = 150 \; V; V_{\mathit{BB}} = \, -5 \; V; \\ L_{\mathit{B}} = 1 \; \mu H; L_{\mathit{C}} = 200 \; \mu H \end{split}$$

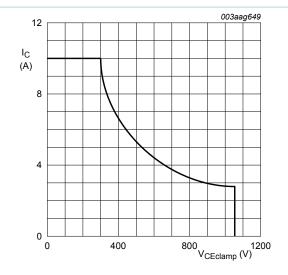


Fig. 2. Reverse bias safe operating area

$$T_j \leq T_{j(max)}$$

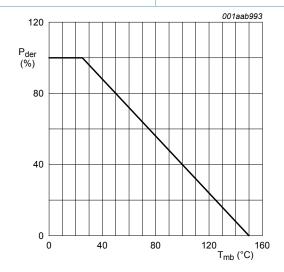
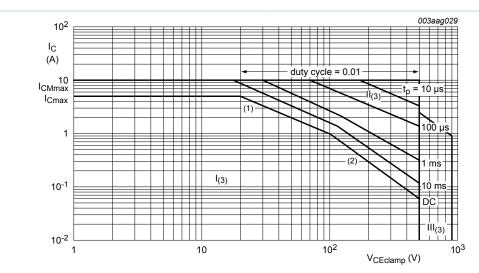


Fig. 3. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

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- (1) P_{tot} maximum and P_{tot} peak maximum lines.
- (2) Second breakdown limits.
- (3) I = Region of permissible DC operation.
- II = Extension for repetitive pulse operation.
- III = Extension during turn-on in single transistor converters provided that $R_{BE} \le 100 \Omega$ and $t_p \le 0.6 \mu s$.

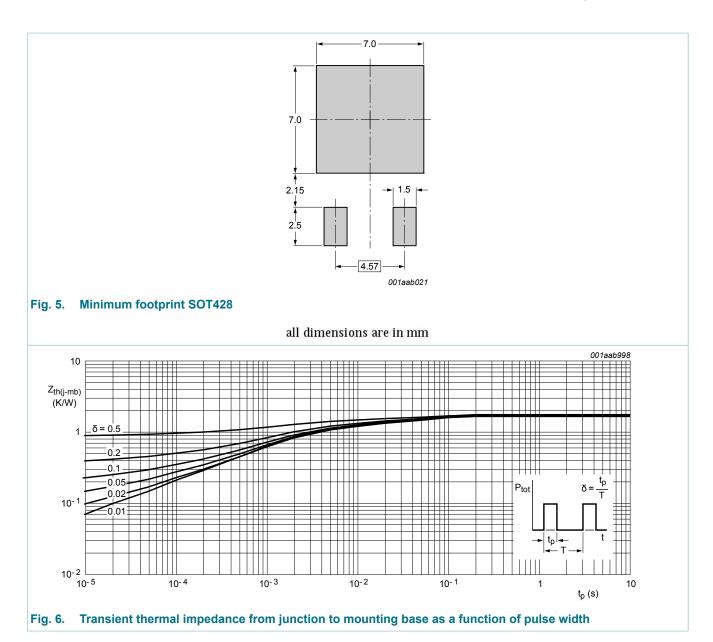
Fig. 4. Forward bias safe operating area for Tmb ≤ 25 °C

5. Thermal characteristics

Table 5. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|---|---|-----|-----|------|------|
| R _{th(j-mb)} | thermal resistance from junction to mounting base | Fig. 6 | - | - | 1.56 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient | printed circuit board (FR4) mounted; minimum footprint; Fig. 5 | - | 75 | - | K/W |

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6. Characteristics

Table 6. Characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|------------------|-----------------------------------|---|-----|-----|-----|-----|------|
| Static char | acteristics | | | | | | |
| I _{CES} | | V _{BE} = 0 V; V _{CE} = 1050 V; T _{mb} = 25 °C | [1] | - | - | 1 | mA |
| | current | V _{BE} = 0 V; V _{CE} = 1050 V; T _j = 125 °C | [1] | - | - | 2 | mA |
| I _{CBO} | collector-base cut-off current | $V_{CB} = 1050 \text{ V}; I_E = 0 \text{ A}; T_{mb} = 25 \text{ °C}$ | [1] | - | - | 1 | mA |
| I _{CEO} | collector-emitter cut-off current | $V_{CE} = 400 \text{ V}; I_{B} = 0 \text{ A}; T_{mb} = 25 ^{\circ}\text{C}$ | [1] | - | - | 0.1 | mA |

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| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|--------------------|--------------------------------------|--|----------|------|-----|------|
| I _{EBO} | emitter-base cut-off current | $V_{EB} = 9 \text{ V}; I_{C} = 0 \text{ A}; T_{mb} = 25 ^{\circ}\text{C}$ | - | - | 0.1 | mA |
| V_{CEOsus} | collector-emitter sustaining voltage | I _B = 0 A; I _C = 100 mA; L _C = 25 mH; T _{mb} = 25 °C; <u>Fig. 7</u> ; <u>Fig. 8</u> | 400 | - | - | V |
| V _{CEsat} | collector-emitter saturation voltage | I _C = 1 A; I _B = 0.2 A; T _{mb} = 25 °C; <u>Fig. 9</u> ; <u>Fig. 10</u> | - | - | 0.5 | V |
| | | I _C = 3 A; I _B = 1 A; T _{mb} = 25 °C; <u>Fig. 9</u> ; <u>Fig. 10</u> | - | 0.25 | 1.5 | V |
| V _{BEsat} | base-emitter saturation voltage | I _C = 3 A; I _B = 1 A; T _{mb} = 25 °C; <u>Fig. 11</u> | - | 1 | 1.5 | V |
| h _{FE} | DC current gain | I_C = 10 mA; V_{CE} = 3 V; T_{mb} = 25 °C; Fig. 12 | 28 | 34 | 47 | |
| | | I_C = 250 mA; V_{CE} = 3 V; T_{mb} = 25 °C; Fig. 12 | 35 | 43 | 57 | |
| | | I _C = 800 mA; V _{CE} = 3 V; T _{mb} = 25 °C; Fig. 12 | 31 | 37 | 48 | |
| Dynamic CI | haracteristics (switching ti | mes - resistive load) | | | | , |
| t _{on} | turn-on time | I _C = 2.5 A; I _{Bon} = 0.5 A; I _{Boff} = -1 A; | - | 1 | - | ms |
| ts | turn-off delay time | $R_L = 100 \Omega$; $V_{CC} = 250 V$; $T_j = 25 °C$; | - | 2.5 | - | ms |
| t _f | fall time | Fig. 13; Fig. 14 | - | 0.3 | - | ms |
| Dynamic CI | haracteristics (switching ti | mes - inductive load) | <u> </u> | | | |
| t _s | turn-off delay time | I_C = 2.5 A; I_{Bon} = 0.5 A; V_{CC} = 350 V; V_{BB} = -5 V; L_B = 1 μ H; T_j = 25 °C; Fig. 15; Fig. 16 | - | 2 | - | ms |
| t _s | turn-off delay time | I_C = 2.5 A; I_{Bon} = 0.5 A; V_{CC} = 350 V; V_{BB} = -5 V; L_B = 1 μ H; T_j = 100 °C; Fig. 15; Fig. 16 | - | 3 | - | ms |
| t _f | fall time | I_C = 2.5 A; I_{Bon} = 0.5 A; V_{CC} = 350 V; V_{BB} = -5 V; L_B = 1 μ H; T_j = 25 °C; Fig. 15; Fig. 16 | - | 200 | - | ns |
| | | I_C 2.5 A; I_{Bon} = 0.5 A; V_{CC} = 350 V; V_{BB} = -5 V; L_B = 1 μ H; T_j = 100 °C; Fig. 15; Fig. 16 | - | 300 | - | ns |

^[1] Measured with half-sine wave voltage (curve tracer).

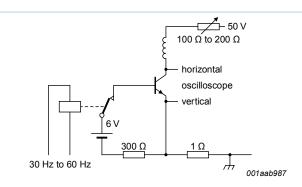


Fig. 7. Test circuit for collector-emitter sustaining voltage

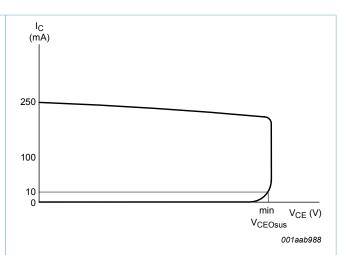


Fig. 8. Oscilloscope display for collector-emitter sustaining voltage test waveform

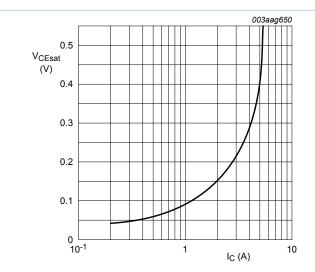


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

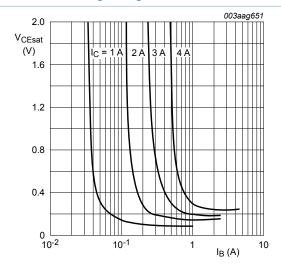


Fig. 10. Collector-emitter saturation voltage as a function of base current; typical values

$$T_j = 25 \, ^{\circ}C$$

10²

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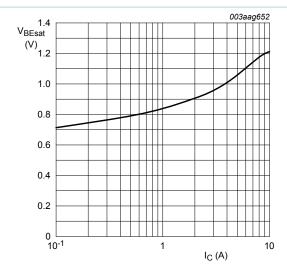
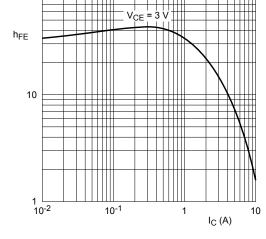


Fig. 11. Base-emitter saturation voltage as a function of Fig. 12. DC current gain as a function of collector collector current; typical values

 $I_C/I_B = 4$



current; typical values

$$V_{CC}$$
 R_L
 V_{IM}
 0
 t_p
 T_{T-1}
 $001aab989$

Fig. 13. Test circuit for resistive load switching

$$V_{IM}=-6$$
 to $+8$ V ; $V_{CC}=250$ V ; $t_p=20$ μs ; $\delta=\frac{t_p}{T}=0.01$ R_B and R_L calculated from I_{Con} and I_{Bon} requirements.

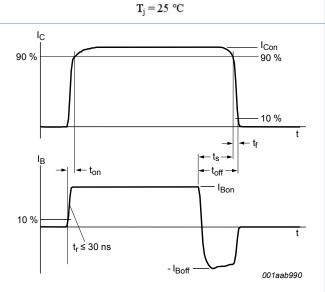


Fig. 14. Switching times waveforms for resistive load

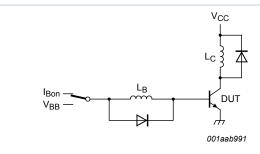


Fig. 15. Test circuit for inductive load switching

$$V_{CC} = 300 \ V; V_{BB} = -5 \ V; L_{C} = 200 \ \mu H; L_{B} = 1 \ \mu H$$

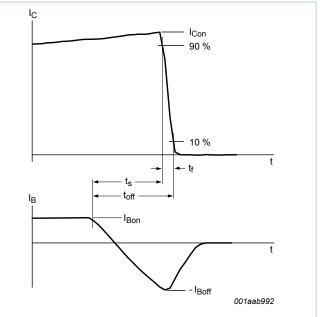


Fig. 16. Switching times waveforms for inductive load

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7. Package outline

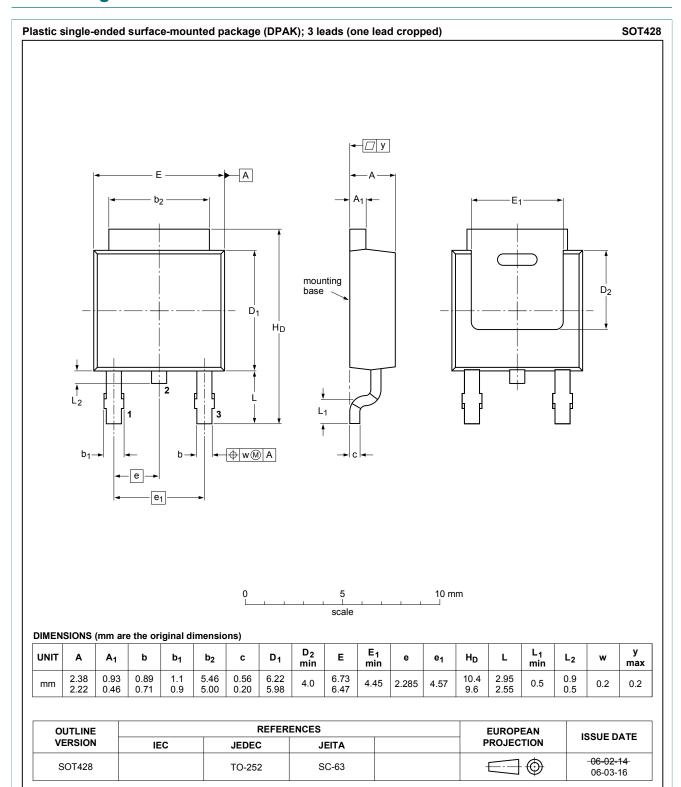


Fig. 17. Package outline DPAK (SOT428)

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